	Туре	Hits	Search Text	DBs
			((field with effect) or FET)	
Н	BRS	1473	and (metal with gate) and	US-PGPUB; USPAT
			(conform\$5 with deposit\$3)	
	į			US-PGPUB;
			((field with effect) or FET)	USPAT; USOCR;
N	BRS	1501	and (metal with gate) and	EPO; JPO;
			(conform\$5 with deposit\$3)	DERWENT;
				IBM TDB
				US-PGPUB;
			oz alla (collancité mich seed	USPAT; USOCR;
ω	BRS	0	with rayer, and	EPO; JPO;
			(erectropracas with date with	DERWENT;
			IIIecar)	IBM TDB
				US-PGPUB;
			S2 and (conductive with seed	USPAT; USOCR;
4	BRS	0	with layer) and	EPO; JPO;
		•	(electroplat\$3 with gate)	DERWENT;
			•	IBM TDB

	Туре	Hits	Search Text	DBs
Л	ე ე	J.	(conductive with seed with	US-PGPUB; USPAT; USOCR;
G	BRS	3	layer) and (electroplat\$3 with gate with metal)	EPO; JPO; DERWENT; IBM_TDB
0	IS&R	1	("5912492").PN.	USPAT
7	BRS	1501	((field with effect) or FET) and (metal with gate) and (conform\$5 with deposit\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT;
				IBM TDB
			(conductive with seed with	US-PGPUB; USPAT; USOCR;
00	BRS	ω	layer) and (electroplat\$3 with gate with metal)	EPO; JPO; DERWENT;
				IBM TDB
				US-PGPUB;
	•			USPAT; USOCR;
9	BRS	0	S7 and S8	EPO; JPO;
				DERWENT;
				IBM_TDB

*	Туре	Hits	Search Text	DBs
				GETT HERE.
				USPAT; USOCR;
10	BRS	33	S7 and seed and electroplat\$3	EPO; JPO;
				DERWENT;
				IBM TDB
				: SUPPR-SU
			ガチザン コカム (いつか)	USPAT; USOCR;
11	BRS	2387	FER OF FER) AND (WORK	EPO; JPO;
		•	אירוו דמווכנדטוו/ מוזמ למנפ	DERWENT;
				IBM_TDB
				US-PGPUB;
			中中中 うちん (いつなと うん)・	USPAT; USOCR;
12	BRS	1811	of FET and (Work ad)	EPO; JPO;
			מווע לפרפ	DERWENT;
				IBM TDB
	•			us-PGPUB;
				USPAT; USOCR;
13	BRS	391	S12 and PMOS and NMOS	EPO; JPO;
				DERWENT;
		-		IBM_TDB

	Туре	Hits	Search Text	DBs
				US-PGPUB;
		>	S14 and (gate with	USPAI; USOCK;
14	BRS	9		EPO; JPO;
•		_	ETECTOPIACAO)	DERWENT;
				IBM_TDB
				US-PGPUB;
				USPAT; USOCR;
15	BRS	302	S13 and (metal with gate)	EPO; JPO;
				DERWENT;
				IBM TDB
16	IS&R		("6015747").PN.	USPAT
				US-PGPUB;
			+ b	USPAT; USOCR;
17	BRS	69	Olostroplates	EPO; JPO;
			GT GCT CT C	DERWENT;
				IBM TDB
				US-PGPUB;
				USPAT; USOCR;
18	BRS	2387	_	EPO; JPO;
			MICH THICKTOIL) AND GAVE	DERWENT;
				IBM TDB

	Туре	Hits	Search Text	DBs
				US-PGPUB;
				USPAT; USOCR;
19	BRS	58	S18 and Ru and Ta and alloy	EPO; JPO;
				DERWENT;
				IBM TDB
				US-PGPUB;
)	USPAT; USOCR;
20	BRS	19	a (ya mili id	EPO; JPO;
			alloy)	DERWENT;
				IBM TDB
				US-PGPUB;
	•			USPAT; USOCR;
21	BRS	4	S18 and (Ru-Ta adj alloy)	EPO; JPO;
				DERWENT;
		*		IBM TDB
22	BRS	28	MOSFET with (gate adj size)	US-PGPUB; USPAT
23	BRS	449	(CMOS with gate with size)	US-PGPUB; USPAT
24	BRS	10258	gate with dimension	US-PGPUB; USPAT

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	Туре	Hits	Search Text	DBs	
25	BRS	768	gate adj dimension	US-PGPUB; USPAT	USPAT
26	BRS	30	MOSFET with gate adj dimension	US-PGPUB; USPAT	USPAT
27	BRS	1.0	through-mask adj electroplating	US-PGPUB; USPAT	USPAT
28	BRS	11,5	damascene with electroplating	US-PGPUB;	USPAT
29	BRS	350	S28 and (seed adj layer)	US-PGPUB;	USPAT
30	BRS	77	electroplating with Ru	US-PGPUB;	USPAT
31	BRS	41	S30 and (seed adj layer)	US-PGPUB;	USPAT
32	IS&R	<u>}</u> }	("6204103").PN.	USPĀT	
33	BRS	171	MOSFET with (work adj function)	US-PGPUB; USPAT	USPAT
34	BRS	9	S33 and Intel	US-PGPUB;	USPAT
35	BRS	8.0	Lin.IN. and (work adj function)	US-PGPUB;	USPAT

	Туре	Hits	Search Text	DBs
36	BRS	0	S35 and Intel	US-PGPUB; USPAT
37	BRS	0	Linn.IN. and (work adj function)	US-PGPUB; USPAT
38	BRS	136	Intel and (work adj function) US-PGPUB; USPAT	US-PGPUB; USPAT
39	BRS	31:18	257/204.ccls. or 438/197- 199,217,218,587,642.ccls.	US-PGPUB; USPAT
40	BRS	237	S39 and (work with function)	US-PGPUB; USPAT
41	BRS	182	S40 and (gate with (metal or alloy))	US-PGPUB; USPAT